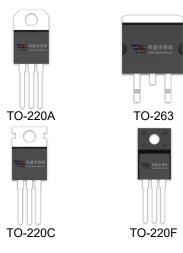


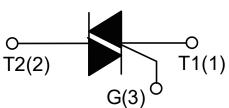
### **DESCRIPTION:**

The BT139X-600E SCR series with the parallel resistor between Gate and Cathode are especially recommended for use on straight hair, igniter, anion generator, etc.



#### **MAIN FEATURES**

Symbol	Value	Unit	
I <sub>T(RMS)</sub>	16	А	
V <sub>DRM</sub> /V <sub>RRM</sub>	600 and 800	V	



### **ABSOLUTE MAXIMUM RATINGS**

Parameter		Symbol	Value	Unit
Storage junction temperature range		T <sub>stg</sub>	-40-150	$^{\circ}\!\mathbb{C}$
Operating junction temperature range		Tj	-40-125	$^{\circ}\!\mathbb{C}$
Repetitive peak off-sta	te voltage(Tj=25℃)	V <sub>DRM</sub>	600/800	V
Repetitive peak reverse voltage(T <sub>j</sub> =25℃)		V <sub>RRM</sub>	600/800	V
Non repetitive surge peak Off-state voltage		V <sub>DSM</sub>	V <sub>DRM</sub> + 100	V
Non repetitive peak reverse voltage		V <sub>RSM</sub>	V <sub>RRM</sub> + 100	V
	TO-220C(Tc=100°C)		16	
DMS on state current	TO-220F(Ins) (Tc=85℃)			А
RMS on-state current	TO-263 (T <sub>C</sub> =75°C)	T <sub>(RMS)</sub>		
	TO-220A(Ins) (Tc=87℃)			
Non repetitive surge peak on-state current (tp=20ms)		I <sub>TSM</sub>	140	А



I <sup>2</sup> t value for fusing (tp=10ms)	l <sup>2</sup> t	98	A <sup>2</sup> s	
Critical rate of rise of on-state	I - II -III	dI/dt	50	A/µs
current (I <sub>G</sub> =2×I <sub>GT</sub> )	IV		10	
Peak gate current	I <sub>GM</sub>	2	Α	
Average gate power dissipation		P <sub>G(AV)</sub>	0.5	W
Peak gate power		P <sub>GM</sub>	5	W

# **ELECTRICAL CHARACTERISTICS** ( $T_j$ =25 $^{\circ}$ C unless otherwise specified)

Symbol	Test Condition Qu	Quadrant	Quadrant	Value				Hait
Symbol	rest Condition	Quadrant		D	E	F	В	Unit
l <sub>GT</sub>	V <sub>D</sub> =12V R <sub>L</sub> =33Ω	I - II -III	MAN	5	10	25	50	m A
		IV MAX	10	25	70	70	mA	
V <sub>G</sub> T		ALL	MAX	1.3				V
V <sub>GD</sub>	$V_D=V_{DRM} T_j=125$ °C RL=3.3KΩ	ALL	MIN	0.2		V		
IL	I <sub>G</sub> =1.2I <sub>GT</sub>	I - III	MAX	15	30	50	80	· mA
		II - IV		20	40	100	120	
Ін	I <sub>T</sub> =100mA		MAX	10	25	40	60	mA
dV/dt	V <sub>D</sub> =2/3V <sub>DRM</sub> Gate Open T <sub>j</sub> =125℃		MIN	20	50	100	500	V/µs

## **STATIC CHARACTERISTICS**

Symbol	Parameter		Value(MAX)	Unit
V <sub>TM</sub>	I <sub>TM</sub> =20A tp=380μs	Tj=25℃	1.6	V
IDRM	\\-\\-\\-\\\-\\\-\\\-\\\-\\\-\\\-\\\-\	Tj=25℃	5	μA
I <sub>RRM</sub>	VD=VDRM VR=VRRM	Tj=125℃	1	mA

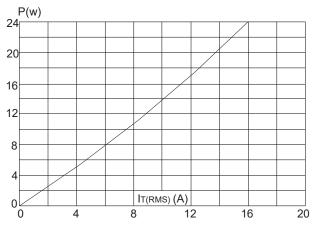


### **THERMAL RESISTANCES**

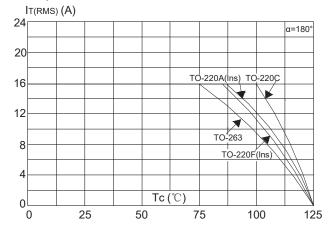
Symbol	Parameter		Value	Unit
R <sub>th(j-c)</sub>	junction to case(AC)	TO-220C	1.2	
		TO-220F(Ins)	2.3	°C/W
		TO-263	2.7	
		TO-220A(Ins)	2.1	



**FIG.1** Maximum power dissipation versus RMS on-state current

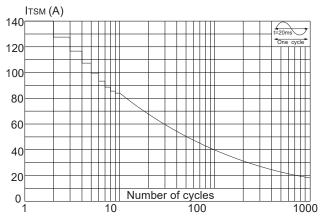


**FIG.2:** RMS on-state current versus case temperature

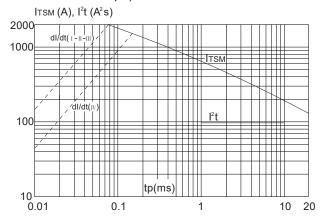




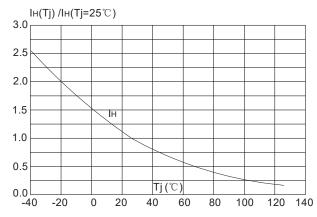
**FIG.3:** Surge peak on-state current versus number of cycles



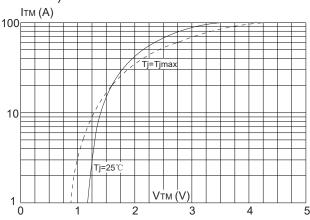
**FIG.5:** Non-repetitive surge peak on-state current for a sinusoidal pulse with width tp<20ms and corresponding value of  $I^2t$  ( I - II - III : dI/dt < 50A/ $\mu$ s; IV:dI/dt < 10A/ $\mu$ s)



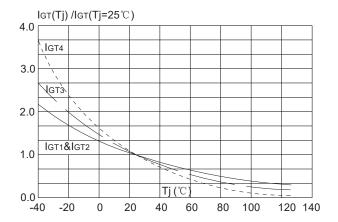
**FIG.7:** Relative variations of holding current versus junction temperature



**FIG.4:** On-state characteristics (maximum values)



**FIG.6:** Relative variations of gate trigger current versus junction temperature



**FIG.8:** Relative variations of latching current versus junction temperature

